TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

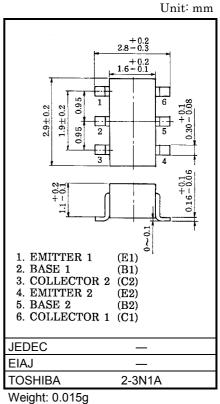
# HN1A01F

Audio Frequency General Purpose Amplifier Applications

- Small package (dual type) •
- High voltage and high current
  - $: V_{CEO} = -50V, I_C = -150mA (max)$
- High hFE:  $hFE = 120 \sim 400$ Excellent hFE linearity •
  - $h_{FE}$  (I<sub>C</sub> = -0.1mA) / h<sub>FE</sub> (I<sub>C</sub> = -2mA) = 0.95 (typ.)

#### Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	Ι <sub>C</sub>	-150	mA
Base current	Ι <sub>Β</sub>	-30	mA
Collector power dissipation	P <sub>C</sub> *	300	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C



\* Total rating

### Electrical Characteristics (Ta = 25°C) (Q1,Q2 Common)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	-	$V_{CB} = -50V, I_E = 0$	_	_	-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	-	$V_{EB} = -5V, I_{C} = 0$	_	_	-0.1	μA
DC current gain	h <sub>FE (note)</sub>	_	$V_{CE} = -6V, I_C = -2mA$	120	_	400	_
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	-	I <sub>C</sub> = −100mA, I <sub>B</sub> = −10mA	_	-0.1	-0.3	V
Transition frequency	f <sub>T</sub>	_	V <sub>CE</sub> = −10V, I <sub>C</sub> = −1mA	80	_	_	MHz
Collector output capacitance	C <sub>ob</sub>	_	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz	_	4	7	pF

Note: hFE Classification

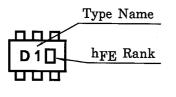
Y (Y): 120~240, GR (G): 200~400

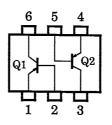
( ) Marking Symbol

# **TOSHIBA**

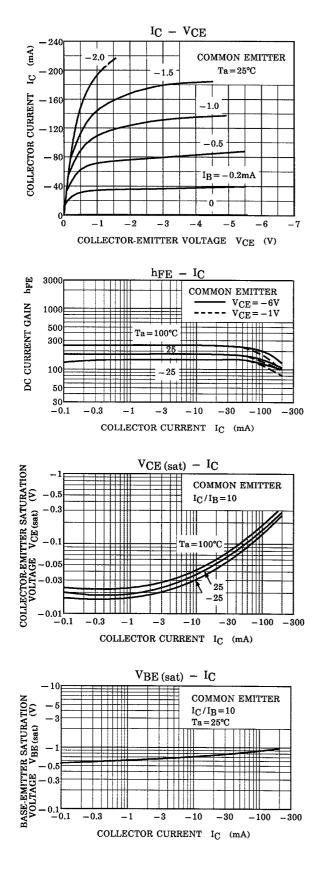
## Marking

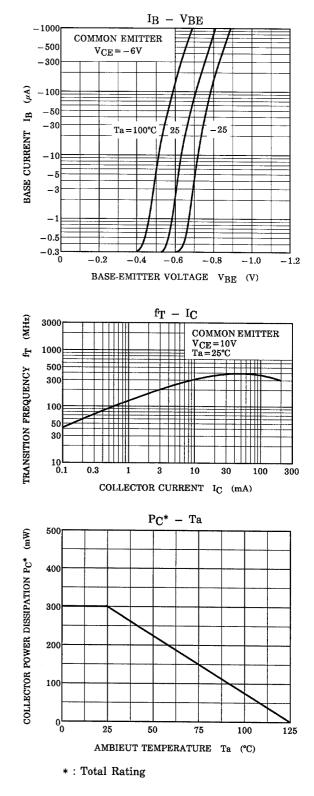
## Equivalent Circuit (Top View)





(Q1,Q2 Common)





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